



## Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit	
<b>Common Ratings</b> ( $T_A=25^{\circ}\text{C}$ Unless Otherwise Noted)				
$V_{\text{DSS}}$	Drain-Source Voltage	20	V	
$V_{\text{GSS}}$	Gate-Source Voltage	$\pm 16$		
$T_{\text{J}}$	Maximum Junction Temperature	150	$^{\circ}\text{C}$	
$T_{\text{STG}}$	Storage Temperature Range	-55 to 150	$^{\circ}\text{C}$	
$I_{\text{S}}$	Diode Continuous Forward Current	$T_{\text{C}}=25^{\circ}\text{C}$ 3.5	A	
<b>Mounted on Large Heat Sink</b>				
$I_{\text{DP}}$	300 $\mu\text{s}$ Pulse Drain Current Tested	$T_{\text{C}}=25^{\circ}\text{C}$	30	A
		$T_{\text{C}}=100^{\circ}\text{C}$	15	
$I_{\text{D}}$	Continuous Drain Current	$T_{\text{C}}=25^{\circ}\text{C}$	10*	A
		$T_{\text{C}}=100^{\circ}\text{C}$	6	
$P_{\text{D}}$	Maximum Power Dissipation	$T_{\text{C}}=25^{\circ}\text{C}$	50	W
		$T_{\text{C}}=100^{\circ}\text{C}$	20	
$R_{\theta\text{JC}}$	Thermal Resistance-Junction to Case	2.5	$^{\circ}\text{C}/\text{W}$	
<b>Mounted on PCB of 1in<sup>2</sup> Pad Area</b>				
$I_{\text{DP}}$	300 $\mu\text{s}$ Pulse Drain Current Tested	$T_{\text{A}}=25^{\circ}\text{C}$	30	A
		$T_{\text{A}}=100^{\circ}\text{C}$	15	
$I_{\text{D}}$	Continuous Drain Current	$T_{\text{A}}=25^{\circ}\text{C}$	2	A
		$T_{\text{A}}=100^{\circ}\text{C}$	1	
$P_{\text{D}}$	Maximum Power Dissipation	$T_{\text{A}}=25^{\circ}\text{C}$	2.5	W
		$T_{\text{A}}=100^{\circ}\text{C}$	1	
$R_{\theta\text{JA}}$	Thermal Resistance-Junction to Ambient	50	$^{\circ}\text{C}/\text{W}$	
<b>Mounted on PCB of Minimum Footprint</b>				
$I_{\text{DP}}$	300 $\mu\text{s}$ Pulse Drain Current Tested	$T_{\text{A}}=25^{\circ}\text{C}$	30	A
		$T_{\text{A}}=100^{\circ}\text{C}$	15	
$I_{\text{D}}$	Continuous Drain Current	$T_{\text{A}}=25^{\circ}\text{C}$	2	A
		$T_{\text{A}}=100^{\circ}\text{C}$	1	
$P_{\text{D}}$	Maximum Power Dissipation	$T_{\text{A}}=25^{\circ}\text{C}$	1.6	W
		$T_{\text{A}}=100^{\circ}\text{C}$	0.6	
$R_{\theta\text{JA}}$	Thermal Resistance-Junction to Ambient	75	$^{\circ}\text{C}/\text{W}$	

Note:

\* Current limited by bond wire.

## Electrical Characteristics (T<sub>A</sub> = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	APM2055NU			Unit
			Min.	Typ.	Max.	
<b>Static Characteristics</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>DS</sub> =250μA	20			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =16V, V <sub>GS</sub> =0V T <sub>J</sub> =85°C			1 30	μA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>DS</sub> =250μA	0.6	0.9	1.5	V
I <sub>GSS</sub>	Gate Leakage Current	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0V			±100	nA
R <sub>DS(ON)</sub> <sup>a</sup>	Drain-Source On-state Resistance	V <sub>GS</sub> =10V, I <sub>DS</sub> =12A		55	70	mΩ
		V <sub>GS</sub> =4.5V, I <sub>DS</sub> =6A		75	90	
		V <sub>GS</sub> =2.5V, I <sub>DS</sub> =2A		140	160	
<b>Diode Characteristics</b>						
V <sub>SD</sub> <sup>a</sup>	Diode Forward Voltage	I <sub>SD</sub> =2A, V <sub>GS</sub> =0V		0.7	1.3	V
<b>Dynamic Characteristics<sup>b</sup></b>						
R <sub>G</sub>	Gate Resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, F=1MHz		2.5		Ω
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =15V, Frequency=1.0MHz		380		pF
C <sub>oss</sub>	Output Capacitance			120		
C <sub>rss</sub>	Reverse Transfer Capacitance			75		
t <sub>d(ON)</sub>	Turn-on Delay Time	V <sub>DD</sub> =10V, R <sub>L</sub> =10Ω, I <sub>DS</sub> =1A, V <sub>GEN</sub> =4.5V, R <sub>G</sub> =6Ω		5	8	ns
T <sub>r</sub>	Turn-on Rise Time			13	23	
t <sub>d(OFF)</sub>	Turn-off Delay Time			16	24	
T <sub>f</sub>	Turn-off Fall Time			3	5	
<b>Gate Charge Characteristics<sup>b</sup></b>						
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =10V, V <sub>GS</sub> =4.5V, I <sub>DS</sub> =12A		5.4	7	nC
Q <sub>gs</sub>	Gate-Source Charge			1.4		
Q <sub>gd</sub>	Gate-Drain Charge			1.7		

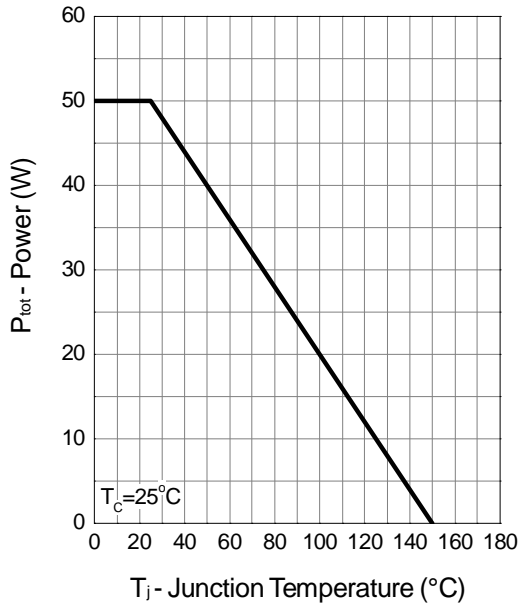
Notes:

a : Pulse test ; pulse width ≤ 300μs, duty cycle ≤ 2%.

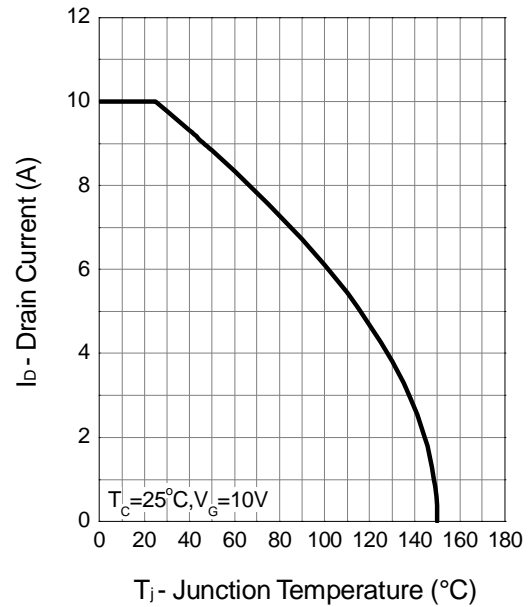
b : Guaranteed by design, not subject to production testing.

## Typical Characteristics

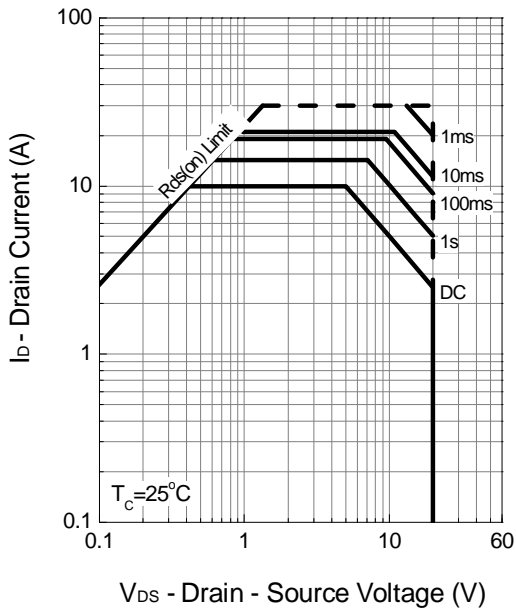
**Power Dissipation**



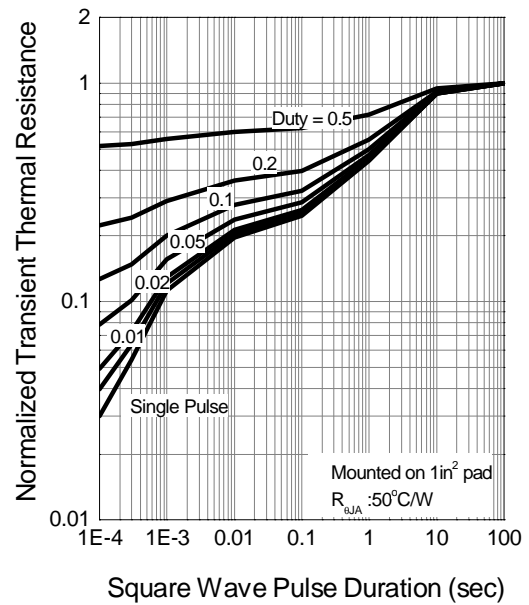
**Drain Current**



**Safe Operation Area**

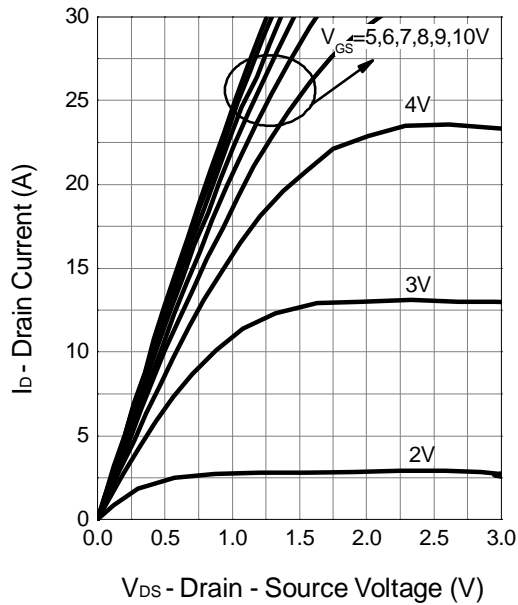


**Thermal Transient Impedance**

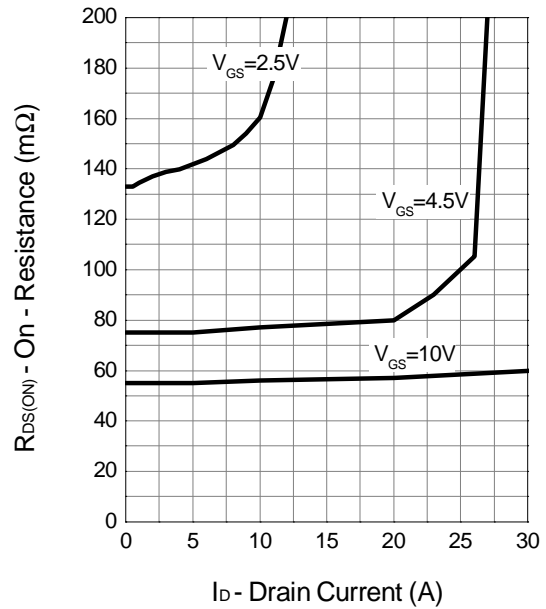


## Typical Characteristics (Cont.)

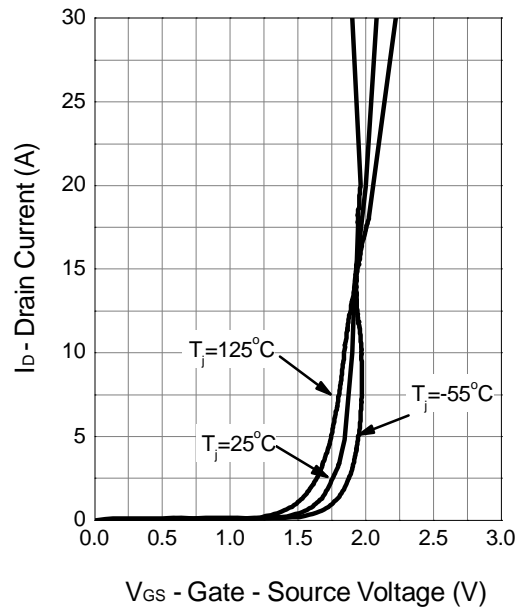
Output Characteristics



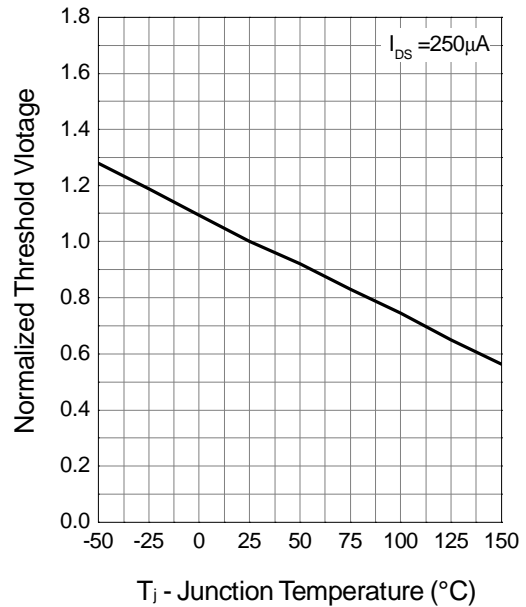
Drain-Source On Resistance



Transfer Characteristics

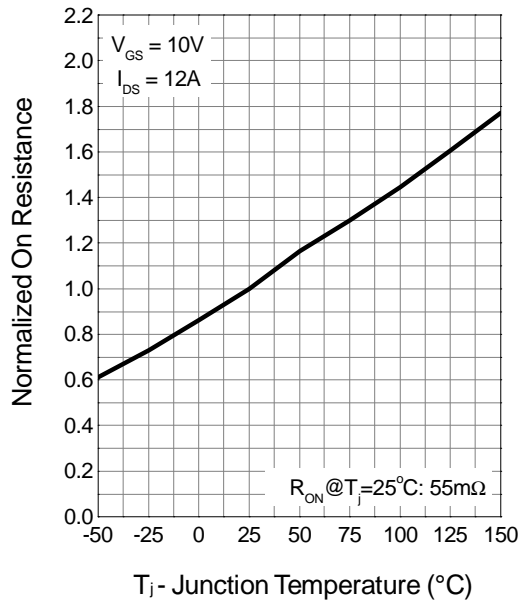


Gate Threshold Voltage

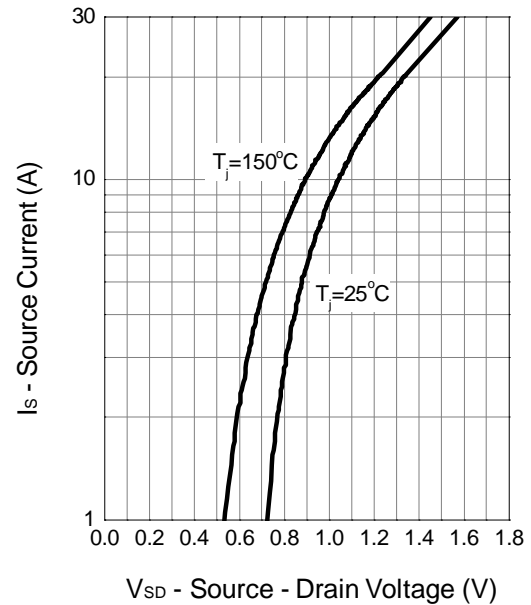


Typical Characteristics (Cont.)

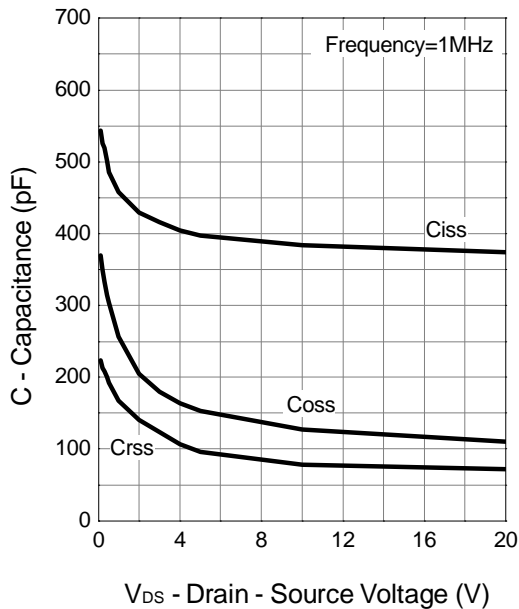
Drain-Source On Resistance



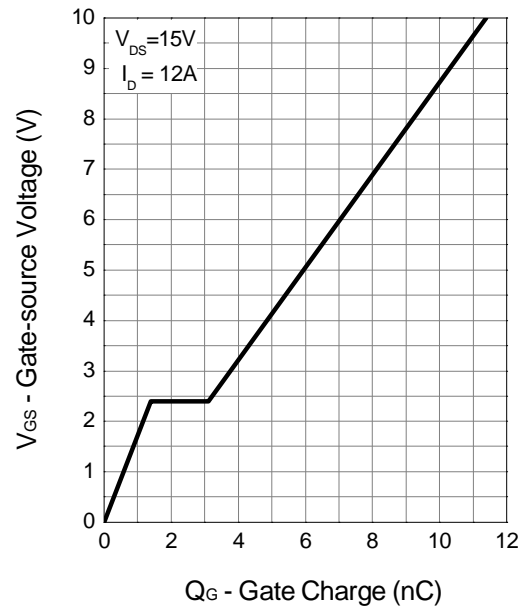
Source-Drain Diode Forward



Capacitance

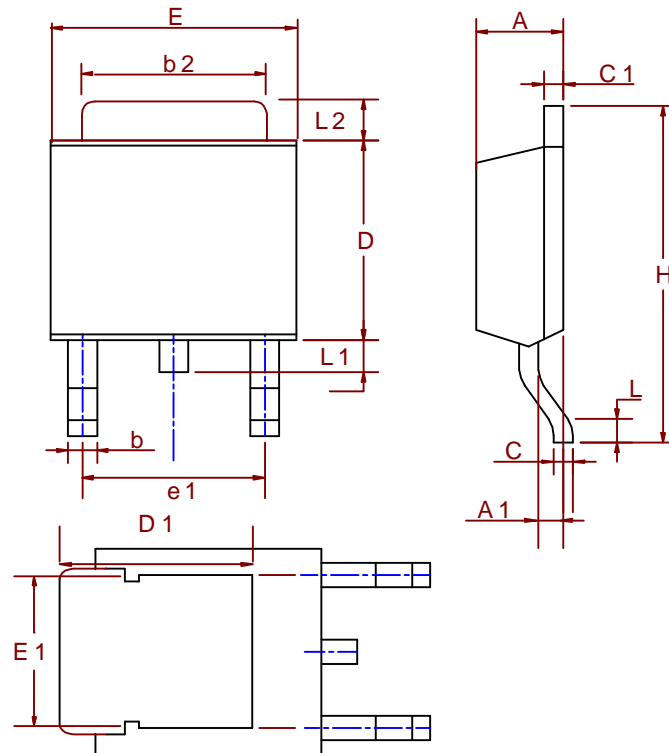


Gate Charge



## Package Information

TO-252 (Reference JEDEC Registration TO-252)

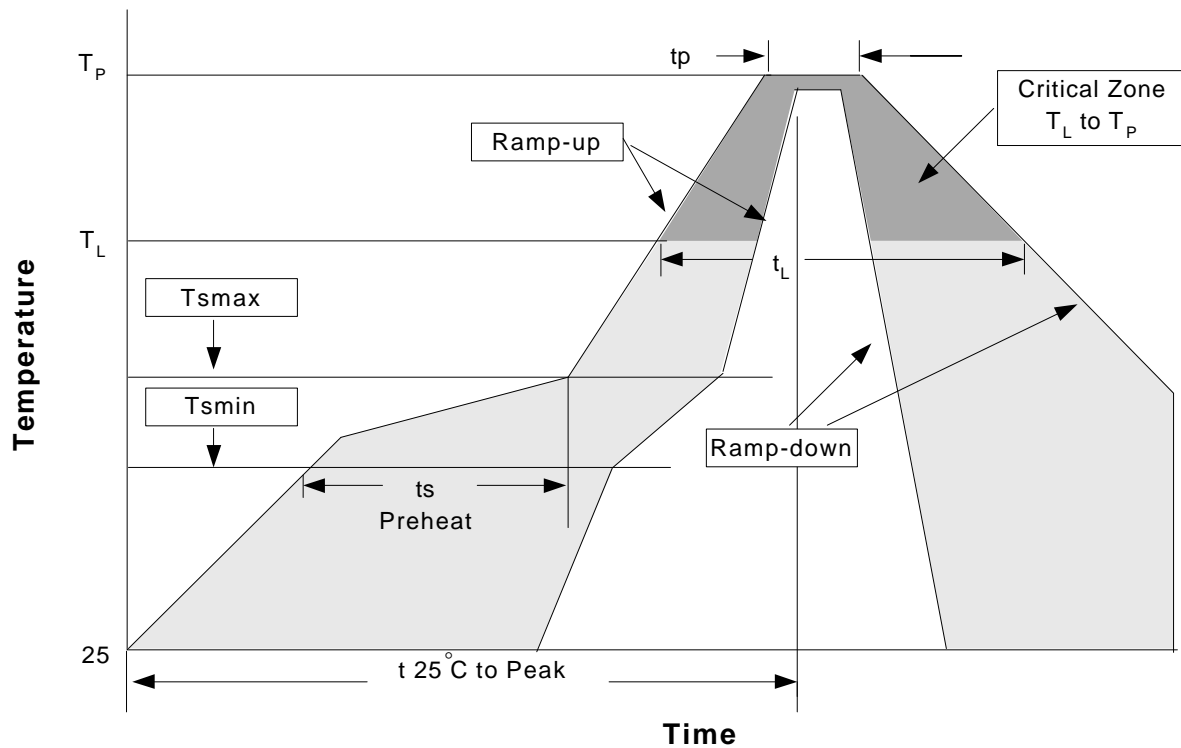


Dim	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	2.18	2.39	0.086	0.094
A1	0.89	1.27	0.035	0.050
b	0.508	0.89	0.020	0.035
b2	5.207	5.461	0.205	0.215
C	0.46	0.58	0.018	0.023
C1	0.46	0.58	0.018	0.023
D	5.334	6.22	0.210	0.245
D1	5.2 REF		0.205 REF	
E	6.35	6.73	0.250	0.265
E1	5.3 REF		0.209 REF	
e1	3.96	5.18	0.156	0.204
H	9.398	10.41	0.370	0.410
L	0.51		0.020	
L1	0.64	1.02	0.025	0.040
L2	0.89	2.032	0.035	0.080

## Physical Specifications

Terminal Material	Solder-Plated Copper (Solder Material : 90/10 or 63/37 SnPb), 100%Sn
Lead Solderability	Meets EIA Specification RSI86-91, ANSI/J-STD-002 Category 3.

### Reflow Condition (IR/Convection or VPR Reflow)



### Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate ( $T_L$ to $T_p$ )	3°C/second max.	3°C/second max.
Preheat		
- Temperature Min ( $T_{smin}$ )	100°C	150°C
- Temperature Max ( $T_{smax}$ )	150°C	200°C
- Time (min to max) ( $t_s$ )	60-120 seconds	60-180 seconds
Time maintained above:		
- Temperature ( $T_L$ )	183°C	217°C
- Time ( $t_L$ )	60-150 seconds	60-150 seconds
Peak/Classification Temperature ( $T_p$ )	See table 1	See table 2
Time within 5°C of actual Peak Temperature ( $t_p$ )	10-30 seconds	20-40 seconds
Ramp-down Rate	6°C/second max.	6°C/second max.
Time 25°C to Peak Temperature	6 minutes max.	8 minutes max.

Notes: All temperatures refer to topside of the package .Measured on the body surface.



## Classification Reflow Profiles(Cont.)

Table 1. SnPb Eutectic Process – Package Peak Reflow Temperatures

Package Thickness	Volume mm <sup>3</sup> <350	Volume mm <sup>3</sup> ≥350
<2.5 mm	240 +0/-5°C	225 +0/-5°C
≥2.5 mm	225 +0/-5°C	225 +0/-5°C

Table 2. Pb-free Process – Package Classification Reflow Temperatures

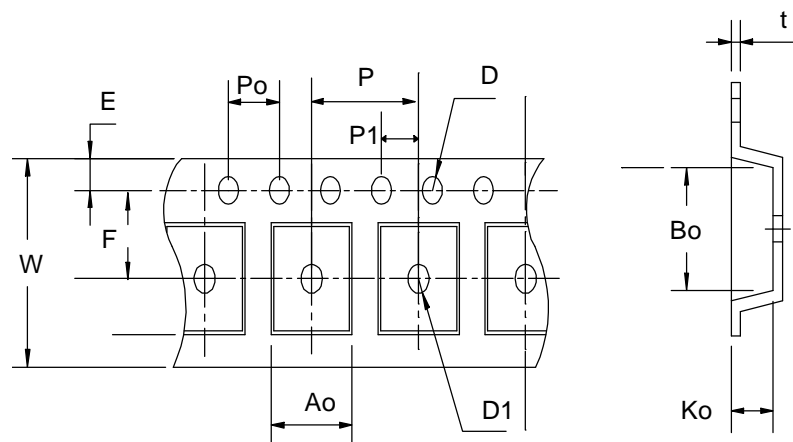
Package Thickness	Volume mm <sup>3</sup> <350	Volume mm <sup>3</sup> 350-2000	Volume mm <sup>3</sup> >2000
<1.6 mm	260 +0°C*	260 +0°C*	260 +0°C*
1.6 mm – 2.5 mm	260 +0°C*	250 +0°C*	245 +0°C*
≥2.5 mm	250 +0°C*	245 +0°C*	245 +0°C*

\*Tolerance: The device manufacturer/supplier **shall** assure process compatibility up to and including the stated classification temperature (this means Peak reflow temperature +0°C. For example 260°C+0°C) at the rated MSL level.

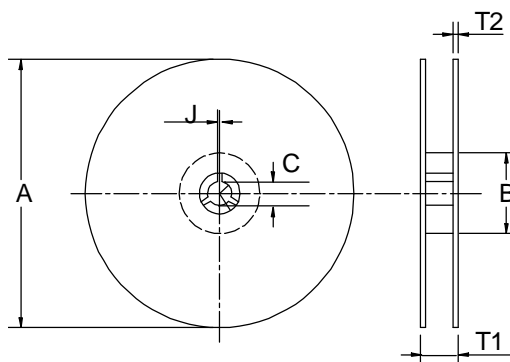
## Reliability Test Program

Test item	Method	Description
SOLDERABILITY	MIL-STD-883D-2003	245°C, 5 SEC
HOLT	MIL-STD 883D-1005.7	1000 Hrs Bias @ 125°C
PCT	JESD-22-B, A102	168 Hrs, 100% RH, 121°C
TST	MIL-STD 883D-1011.9	-65°C ~ 150°C, 200 Cycles

## Carrier Tape & Reel Dimensions



### Carrier Tape & Reel Dimensions (Cont.)



Application	A	B	C	J	T1	T2	W	P	E
TO-252	330 ±3	100 ±2	13 ±0.5	2 ±0.5	16.4 +0.3 -0.2	2.5 ±0.5	16+ 0.3 -0.1	8 ±0.1	1.75 ±0.1
	F	D	D1	Po	P1	Ao	Bo	Ko	t
	7.5 ±0.1	1.5 +0.1	1.5 ±0.25	4.0 ±0.1	2.0 ±0.1	6.8 ±0.1	10.4 ±0.1	2.5 ±0.1	0.3 ±0.05

(mm)

### Cover Tape Dimensions

Application	Carrier Width	Cover Tape Width	Devices Per Reel
TO-252	16	13.3	2500

### Customer Service

**Anpec Electronics Corp.**

Head Office :

No.6, Dusing 1st Road, SBIP,

Hsin-Chu, Taiwan, R.O.C.

Tel : 886-3-5642000

Fax : 886-3-5642050

Taipei Branch :

7F, No. 137, Lane 235, Pac Chiao Rd.,

Hsin Tien City, Taipei Hsien, Taiwan, R. O. C.

Tel : 886-2-89191368

Fax : 886-2-89191369